



YEA SHIN TECHNOLOGY CO., LTD

UF1AS THRU UF1MS

Ultra Fast Recovery Rectifier

VOLTAGE- 50 to 1000 Volts CURRENT - 1.0 Amperes



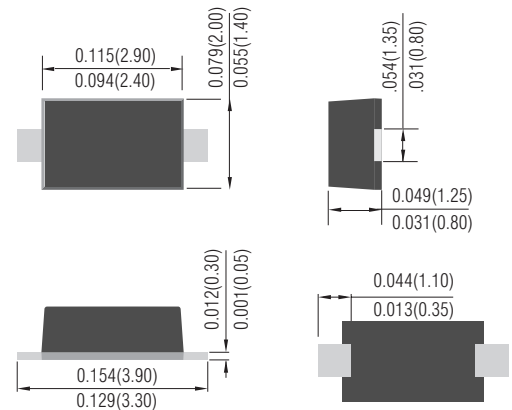
SOD-123S Unit:inch(mm)

FEATURES

- Glass passivated chip
- Ultra fast switching for high efficiency
- For surface mounted applications
- Low forward voltage drop and high current capability
- Low reverse leakage current
- Plastic material has UL flammability classification 94V-0
- High temperature soldering : 260°C / 10 seconds at terminals
- Pb free product at available : 99% Sn above meet RoHS environment substance directive request

MECHANICAL DATA

- Case : Molded plastic
- Polarity : Indicated by cathode band



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

Single phase, half wave, 60Hz, resistive or inductive load.

For capacitive load, derate current by 20%

CHARACTERISTICS	SYMBOL	UF1AS	UF1BS	UF1DS	UF1GS	UF1JS	UF1KS	UF1MS	UNIT
MARKING CODE		U1	U2	U3	U4	U5	U6	U7	
Maximum Recurrent Peak Reverse Voltage	VRRM	50	100	200	400	600	800	1000	V
Maximum RMS Voltage	VRMS	35	70	140	280	420	560	700	V
Maximum DC Blocking Voltage	VDC	50	100	200	400	600	800	1000	V
Maximum Average Forward Rectified Current @TL =75°C	I(AV)	1.0							A
Peak Forward Surge Current 8.3ms single half sine-wave super imposed on rated load (JEDEC METHOD)	IFSM	30							A
Maximum forward Voltage at 1.0A	VF	1.0			1.3	1.5	1.7		V
Maximum DC Reverse Current @TJ =25°C at Rated DC Blocking Voltage @TJ =100°C	IR	5 100							uA
Maximum Reverse Recovery Time (Note 1)	TRR	50				75			ns
Typical Junction Capacitance (Note 2)	CJ	20				10			pF
Typical Thermal Resistance (Note 3)	RθJL	30							°C/W
Operating Temperature Range	TJ	-55 to +150							°C
Storage Temperature Range	TSTG	-55 to +150							°C

NOTES : 1.Reverse Recovery Test Conditions :IF=0.5A,IR=1.0A,IRR=0.25A.

2.Measured at 1.0MHz and applied reverse voltage of 4.0V DC.

3.Thermal Resistance junction to Lead.

DEVICE CHARACTERISTICS

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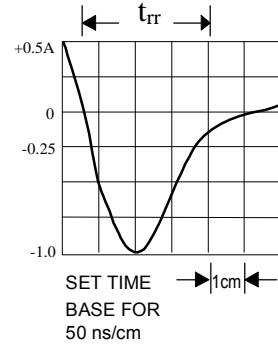
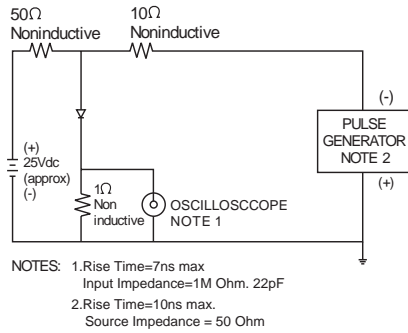


Fig. 1-REVERSE RECOVERY TIME CHARACTERISTIC AND TEST CIRCUIT DIAGRAM

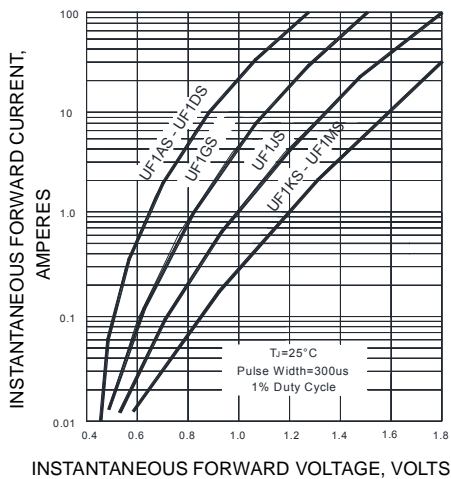


Fig. 2-FORWARD CHARACTERISTICS

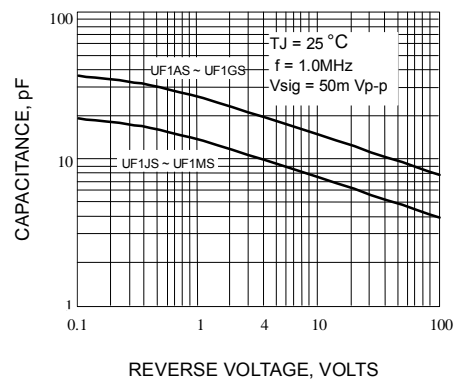


Fig. 3- TYPICAL JUNCTION CAPACITANCE

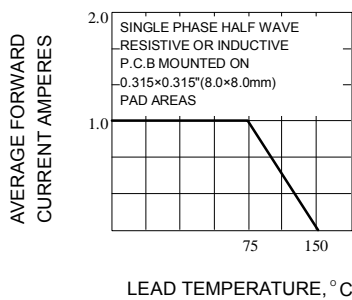


Fig. 4- FORWARD CURRENT DERATING CURVE

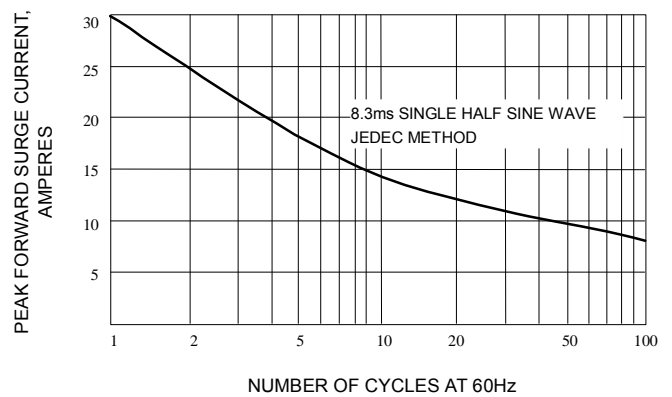


Fig. 5-PEAK FORWARD SURGE CURRENT